



STP40NF10L

N-channel 100V - 0.028Ω - 40A TO-220
Low gate charge STripFET™ Power MOSFET

General features

Type	V _{DSS}	R _{DS(on)}	I _D
STP40NF10L	100V	<0.033Ω	40A

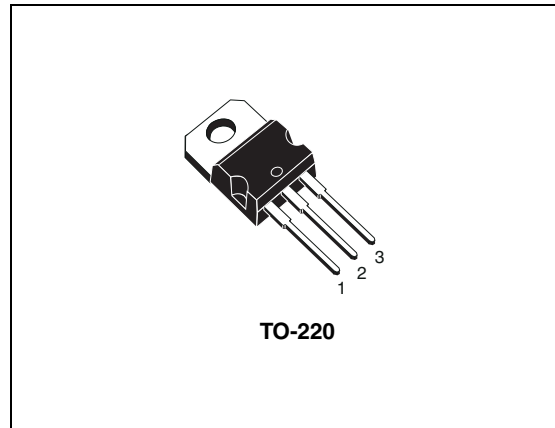
- Exceptional dv/dt capability
- 100% avalanche tested
- Application oriented characterization

Description

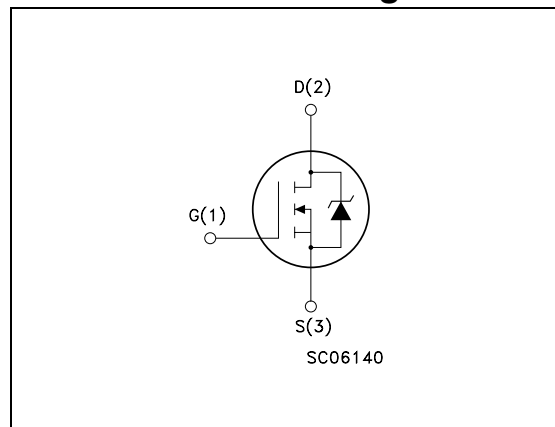
This Power MOSFET series realized with STMicroelectronics unique STripFET process has specifically been designed to minimize input capacitance and gate charge. It is therefore suitable as primary switch in advanced high-efficiency isolated DC-DC converters for Telecom and Computer application. It is also intended for any application with low gate charge drive requirements.

Applications

- Switching application



Internal schematic diagram



Order codes

Part number	Marking	Package	Packaging
STP40NF10L	P40NF10L	TO-220	Tube

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1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($v_{GS} = 0$)	100	V
V_{GS}	Gate- source voltage	± 17	V
I_D	Drain current (continuous) at $T_C = 25^\circ\text{C}$	40	A
I_D	Drain current (continuous) at $T_C = 100^\circ\text{C}$	25	A
$I_{DM}^{(1)}$	Drain current (pulsed)	160	A
P_{TOT}	Total dissipation at $T_C = 25^\circ\text{C}$	150	W
	Derating factor	1	W/ $^\circ\text{C}$
$E_{AS}^{(2)}$	Single pulse avalanche energy	430	mJ
T_{stg}	Storage temperature	- 65 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature	175	

1. Pulse width limited by safe operating area

2. Starting $T_j = 25^\circ\text{C}$, $I_D = 20\text{A}$, $V_{DD} = 40\text{V}$

Table 2. Thermal data

$R_{thj-case}$	Thermal resistance junction-case Max	1	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient Max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE}=25^{\circ}C$ unless otherwise specified)

Table 3. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250 \mu A, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage	$V_{DS} = \text{Max rating}$			1	μA
	Drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}, T_C = 125^{\circ}C$			10	μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 17V$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1	1.7	2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10V, I_D = 20A$		0.028	0.033	Ω
		$V_{GS} = 5V, I_D = 20A$		0.030	0.036	Ω

Table 4. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15V, I_D = 20A$		25		S
C_{iss}	Input capacitance	$V_{DS} = 25V, f = 1 \text{ MHz}, V_{GS} = 0$		2300		pF
C_{oss}	Output capacitance			290		pF
C_{rss}	Reverse transfer capacitance			125		pF
Q_g	Total gate charge	$V_{DD} = 80V, I_D = 40A, V_{GS} = 5V$		46	64	nC
Q_{gs}	Gate-source charge			12		nC
Q_{gd}	Gate-drain charge			22		nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5.

Table 5. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on delay time	$V_{DD} = 50V, I_D = 20A, R_G = 4.7\Omega, V_{GS} = 4.5V$ (see Figure 13)		25		ns
	Rise time			82		ns
$t_{d(off)}$ t_f	Turn-off-delay time	$V_{DD} = 50V, I_D = 20A, R_G = 4.7\Omega, V_{GS} = 4.5V$ (see Figure 13)		64		ns
	Fall time			24		ns
$t_{d(off)}$ t_f t_c	Off-voltage Rise Time	$V_{clamp} = 80V, I_D = 40A, R_G = 4.7\Omega, V_{GS} = 4.5V$ (see Figure 15)		51		ns
	Fall Time			29		ns
	Cross-over time			53		ns

Table 6. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current				40	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)				160	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40A, V_{GS} = 0$			1.3	V
t_{rr}	Reverse recovery time	$I_{SD} = 40A, V_{DD} = 30V$ $di/dt = 100A/\mu s,$ $T_j = 150^\circ C$ (see Figure 15)		110		ns
Q_{rr}	Reverse recovery charge			467		nC
I_{RRM}	Reverse recovery current			8		A

1. Pulse width limited by safe operating area.
2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

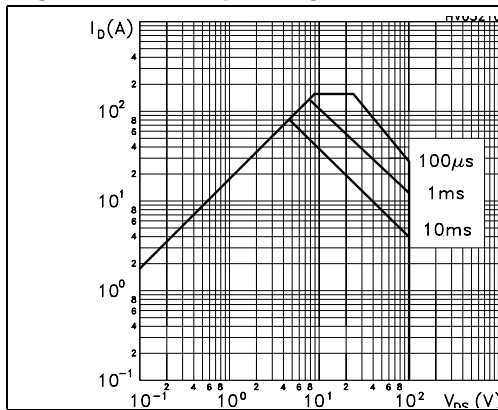


Figure 2. Thermal impedance

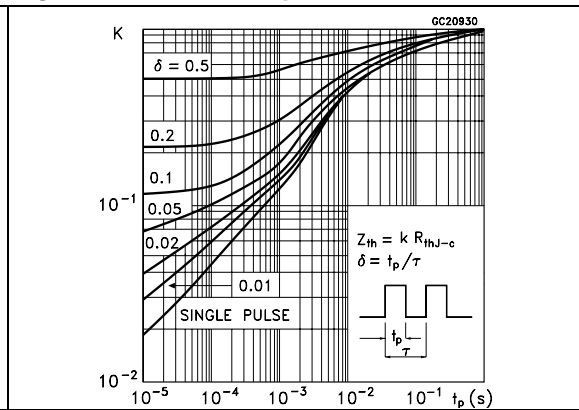


Figure 3. Output characteristics

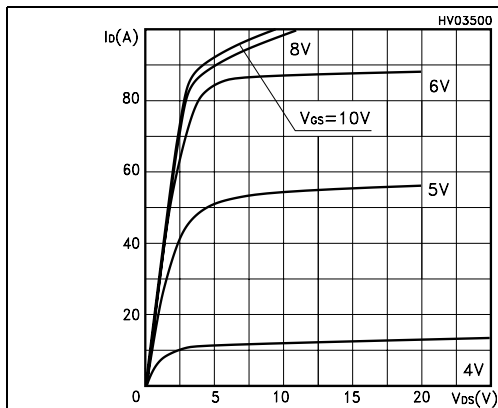


Figure 4. Transfer characteristics

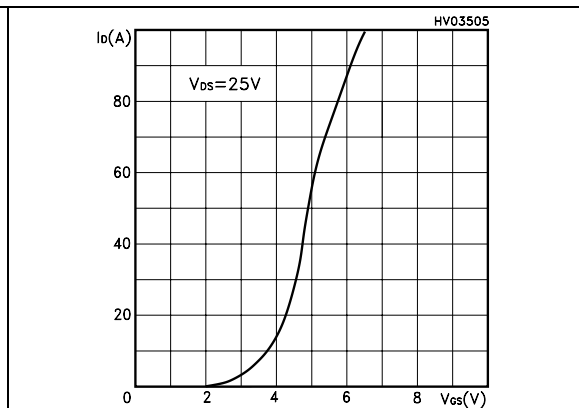


Figure 5. Transconductance

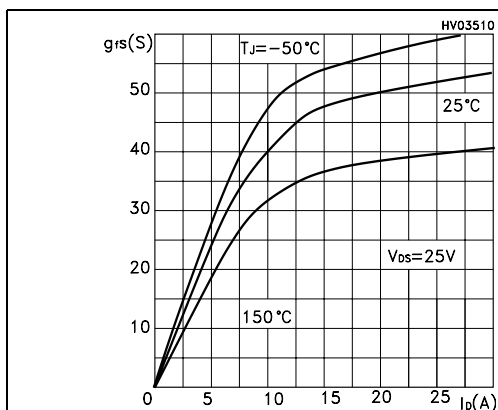


Figure 6. Static drain-source on resistance

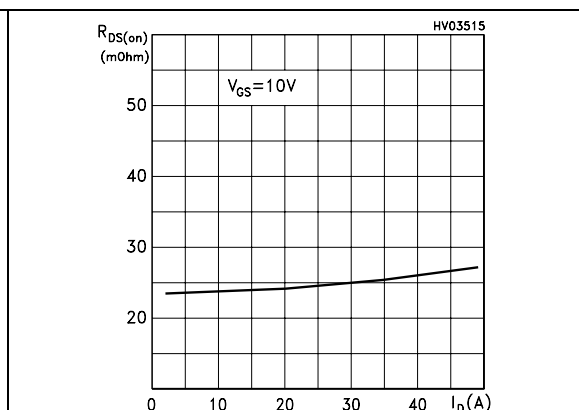


Figure 7. Gate charge vs. gate-source voltage Figure 8. Capacitance variations

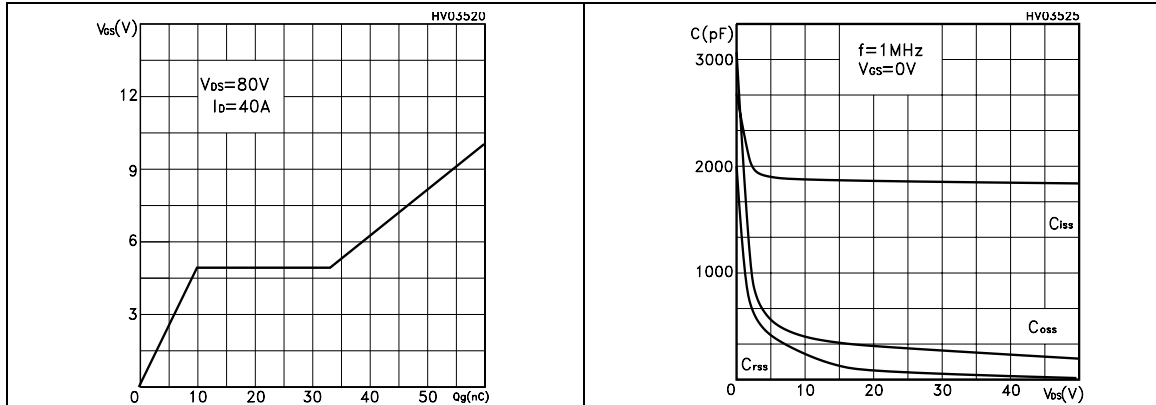


Figure 9. Normalized gate threshold voltage vs. temperature Figure 10. Normalized on resistance vs. temperature

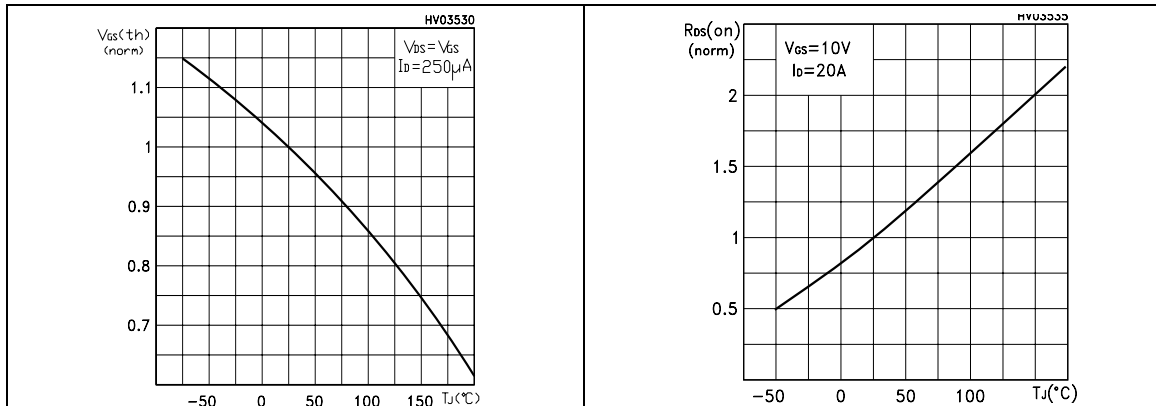
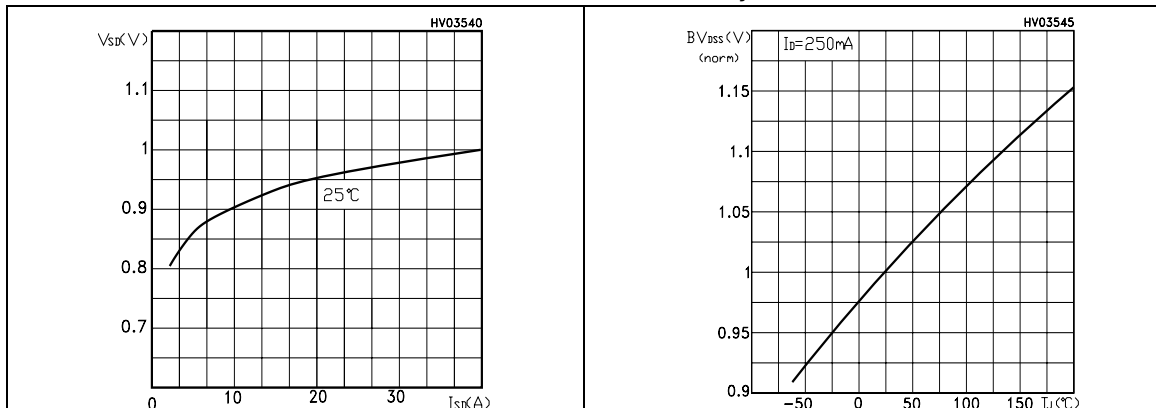


Figure 11. Source-drain diode forward characteristics Figure 12. Normalized breakdown voltage vs. t_j



3 Test circuit

Figure 13. Switching times test circuit for resistive load

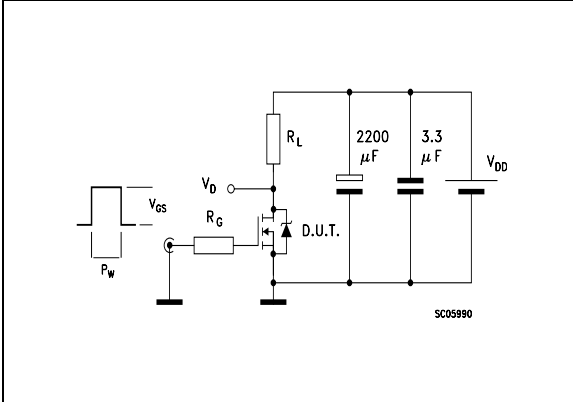


Figure 14. Gate charge test circuit

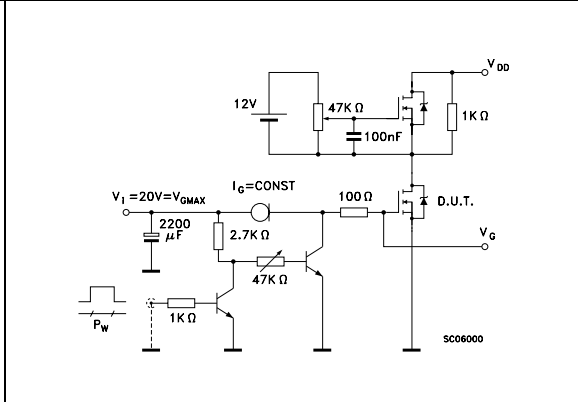


Figure 15. Test circuit for inductive load switching and diode recovery times

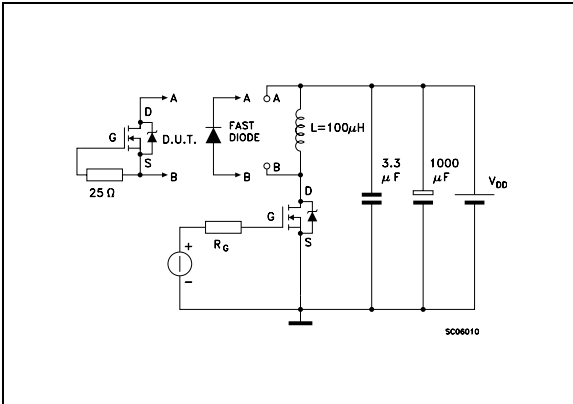


Figure 16. Unclamped Inductive load test circuit

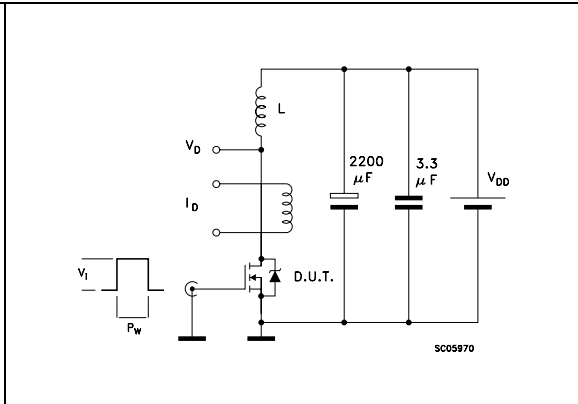


Figure 17. Unclamped inductive waveform

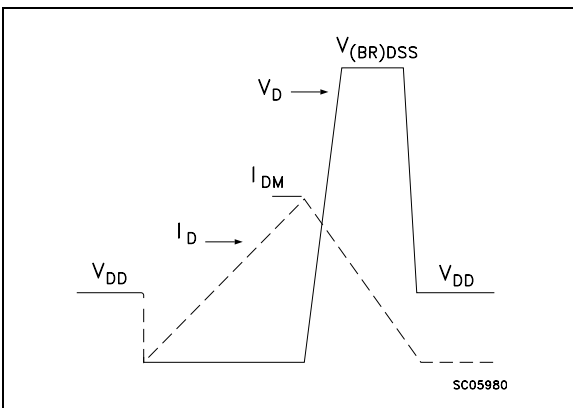
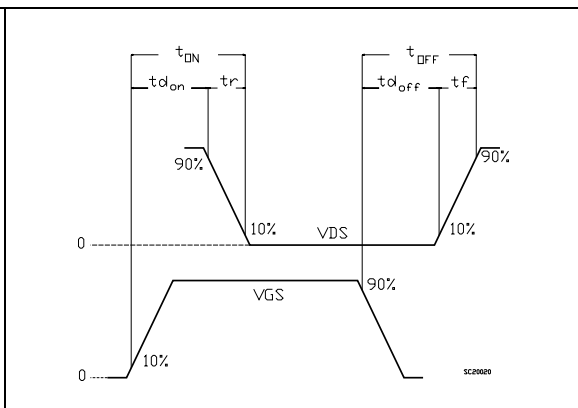


Figure 18. Switching time waveform

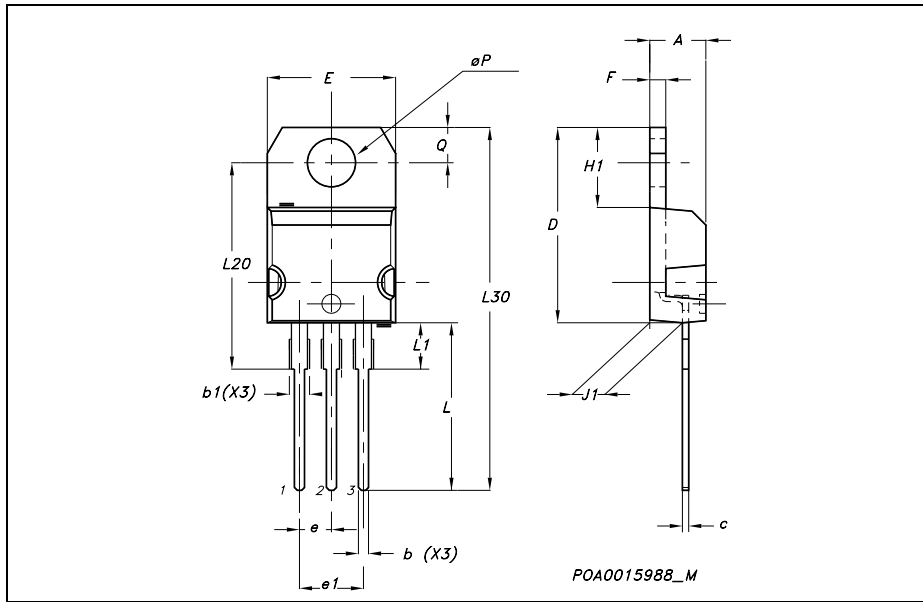


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect. The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at : www.st.com

TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



5 Revision history

Table 7. Revision history

Date	Revision	Changes
09-Sep-2004	1	First version.
17-Aug-2006	2	The document has been reformatted.
31-Jan-2007	3	Typo mistake on Table 1 .

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